

600V 180mohm Super-Junction Power MOSFET
AK3S60N1K8FMF

Description:

This SJ device provides good FOM performance, better EMI for customer application.

Features:

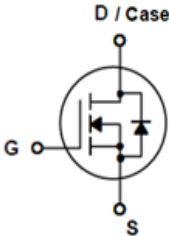
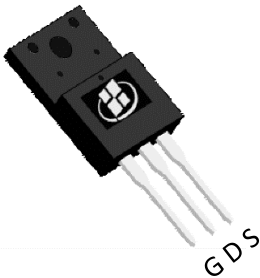
- EMI-Friendly
- RoHS compliant
- Halogen-free

Applications:

- High Frequency Switching
- Quick Charging and Adapter

Key Performance Parameters:

Parameter	Value	Unit
V_{DS}	600	V
$R_{DS(on), max} @V_{GS} = 10\text{ V}$	180	mΩ
I_D	10.5	A



Ordering Information:

Ordering Code	Package Type	Marking Code	Form	Packing
AK3S60N1K8FMF	TO-220F	3S60N1K8FMF	Tube	1000 per box

Maximum Ratings (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{DS}	Drain - Source Voltage	600	V
I _D	Drain Current - Continuous (T _C = 25°C) ^(Note 1)	10.5	A
	Drain Current - Continuous (T _C = 100°C)	6.5	A
I _{DM}	Drain Current - Pulsed ^(Note 2)	31.5	A
V _{GS}	Gate - Source Voltage	± 30	V
E _{AS}	Single Pulsed Avalanche Energy ^(Note 3)	66	mJ
P _D	Power Dissipation (T _C = 25°C)	50	W
dV/dT	MOSFET dv/dt ruggedness, V _{DS} = 0...400 V	70	V/ns
	Reverse diode dv/dt, V _{DS} = 0...400 V	27	V/ns
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C

Thermal Characteristics

Symbol	Parameter	Value	Units
R _{θJC}	Thermal Resistance, Junction - to - Case, Steady State	2.5	°C/W
R _{θJA}	Thermal Resistance, Junction - to - Ambient, Steady State ^(Note 4)	55	°C/W

Notes:

- 1. The max drain current rating limited by maximum junction temperature
- 2. Repetitive Rating: Pulse width limited by maximum junction temperature
- 3. L = 10.8 mH, V_{DD} = 100 V, I_{AS} = 3.5 A, R_G = 25 Ω, Starting T_J = 25 °C
- 4. Mount on minimum PCB layout

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Static Characteristics						
$V_{(BR)DSS}$	Drain - Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	600			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$			10	μA
I_{GSS}	Gate Leakage Current	$V_{GS} = \pm 30\text{ V}, V_{DS} = 0\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	4	5	V
$R_{DS(ON)}$	Drain - Source on - state resistance	$V_{GS} = 10\text{ V}, I_D = 6\text{ A}$		140	180	m Ω

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$		1287		pF
C_{oss}	Output Capacitance			26		pF
C_{rss}	Reverse Transfer Capacitance			3		pF
$C_{o(er)}$	Effective output capacitance, energy related	$V_{DS} = 0\ldots 400\text{ V}, V_{GS} = 0\text{ V}$		48		pF
$C_{o(tr)}$	Effective output capacitance, time related	$V_{DS} = 0\ldots 400\text{ V}, V_{GS} = 0\text{ V},$ $I_D = \text{constant}$		368		pF
R_g	Gate Resistance	$f = 1\text{ MHz}$		19		Ω

Switching Characteristics

$t_{d(on)}$	Turn On Delay Time	$V_{DD} = 400\text{ V}, I_D = 6\text{ A},$ $V_{GS} = 13\text{ V}, R_G = 3.3\text{ }\Omega$		82		ns
t_r	Rise Time			23		ns
$t_{d(off)}$	Turn Off Delay Time			93		ns
t_f	Fall Time			8		ns
Q_g	Total Gate Charge	$V_{DD} = 400\text{ V}, I_D = 6\text{ A},$ $V_{GS} = 10\text{ V}$		32		nC
Q_{gs}	Gate - Source Charge			8		nC
Q_{gd}	Gate - Drain Charge			16		nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Body - Diode Forward Current			10.5	A
I_{SM}	Maximum Pulsed Body - Diode Forward Current			31.5	A
V_{SD}	Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 6\text{ A}$		0.9	V
t_{rr}	Reverse recovery time	$V_{DD} = 400\text{ V}, I_D = 6\text{ A},$ $di/dt = 100\text{ A}/\mu\text{s}$		83	ns
Q_{rr}	Reverse recovery charge			1	μC
I_{rrm}	Peak Reverse Recovery Current			17	A

Electrical Characteristics Diagrams

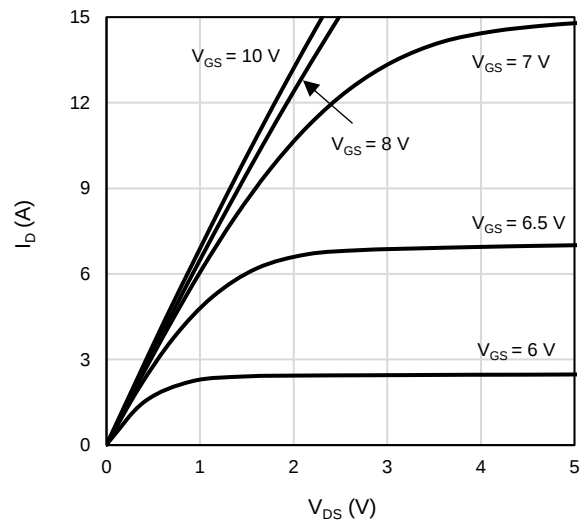


Figure 1: On-Region Characteristics

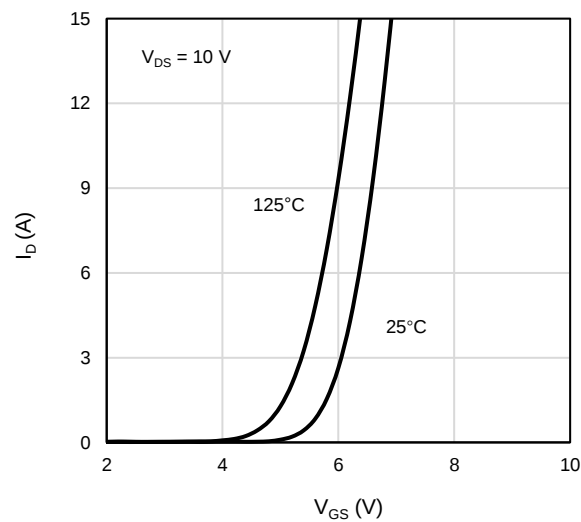


Figure 2: Transfer Characteristics

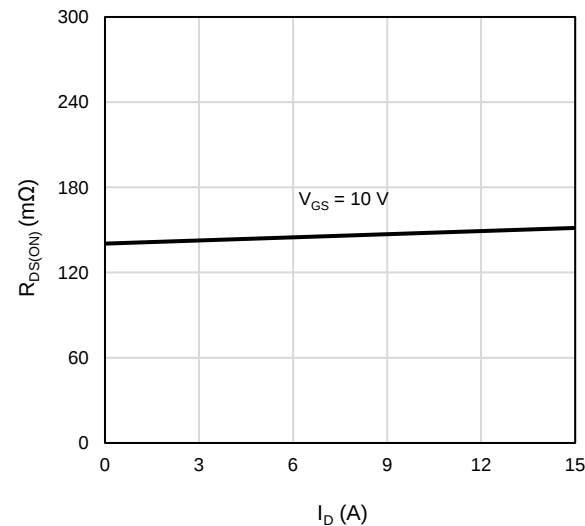


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

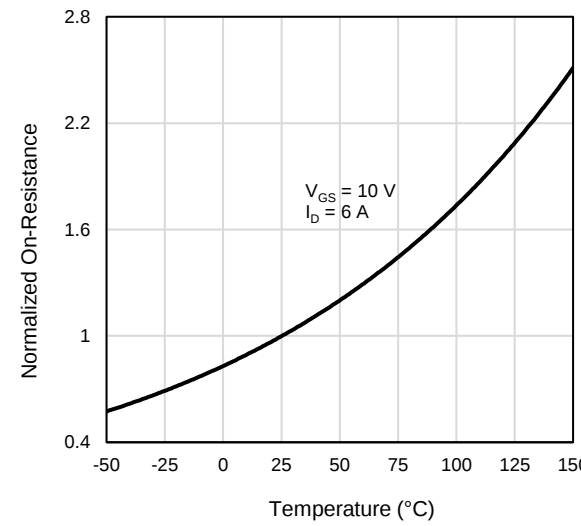


Figure 4: On-Resistance vs. Junction Temperature

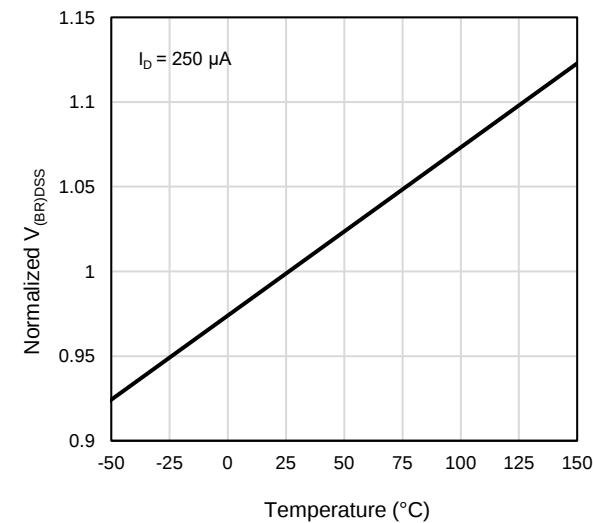


Figure 5: Breakdown Voltage vs. Junction Temperature

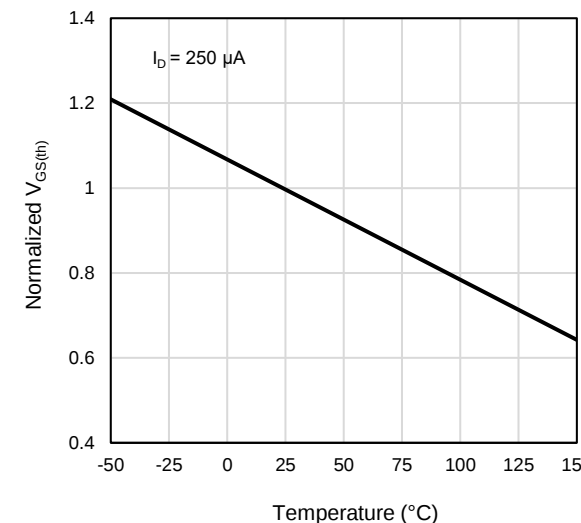


Figure 6: Threshold Voltage vs. Junction Temperature

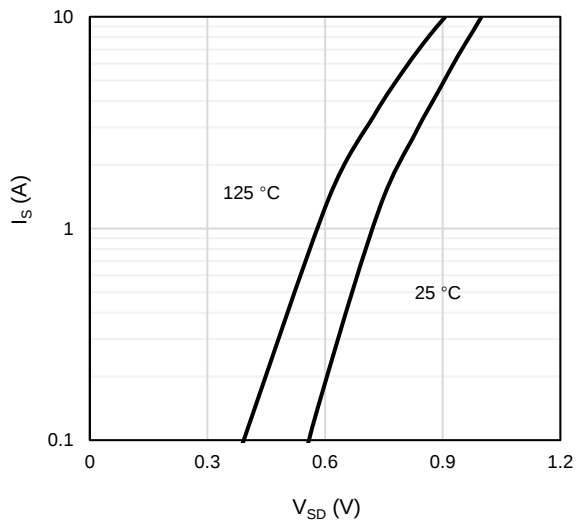


Figure 7: Body-Diode Characteristics

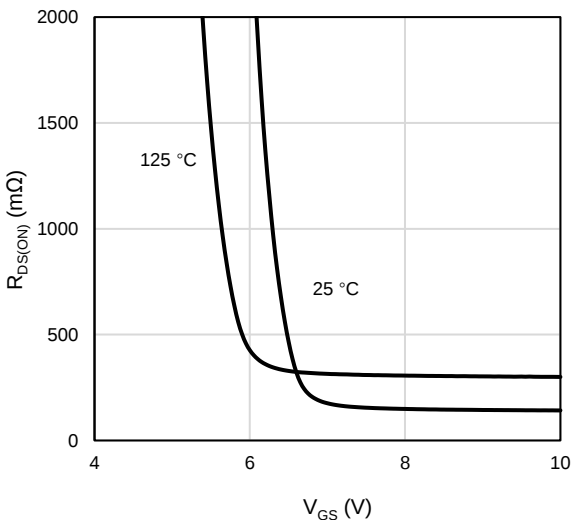


Figure 8: On-Resistance vs. Gate-Source Voltage

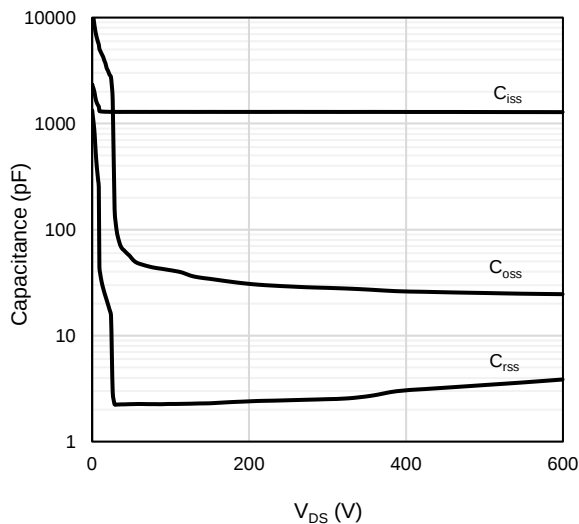


Figure 9: Capacitance Characteristics

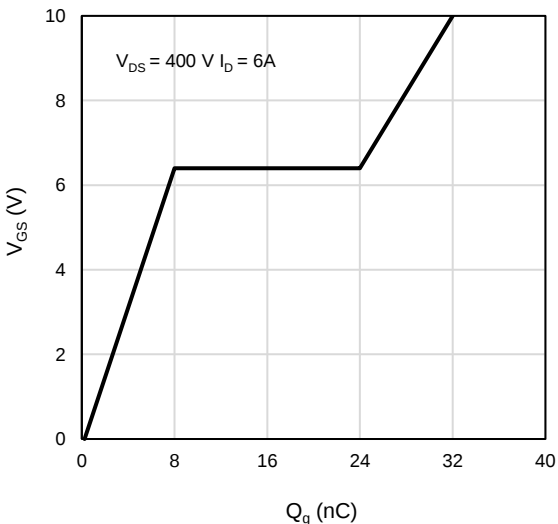


Figure 10: Gate-Charge Characteristics

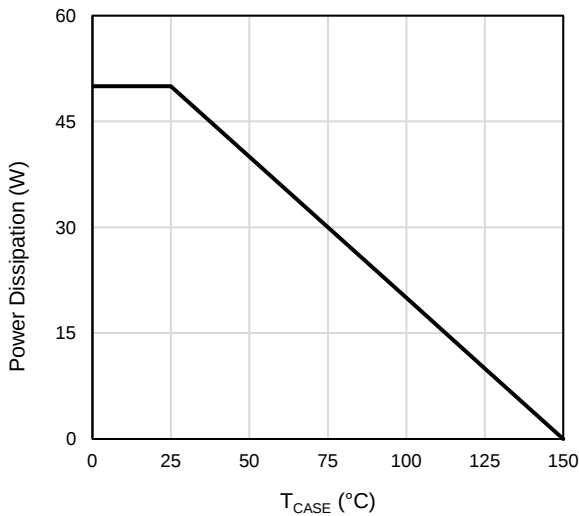


Figure 11: Power De-rating

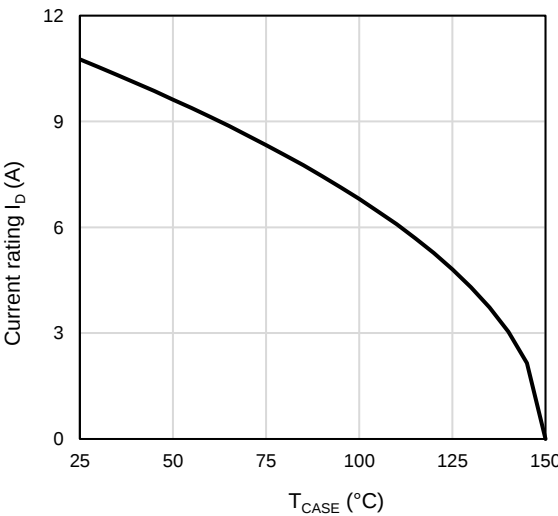


Figure 12: Current De-rating

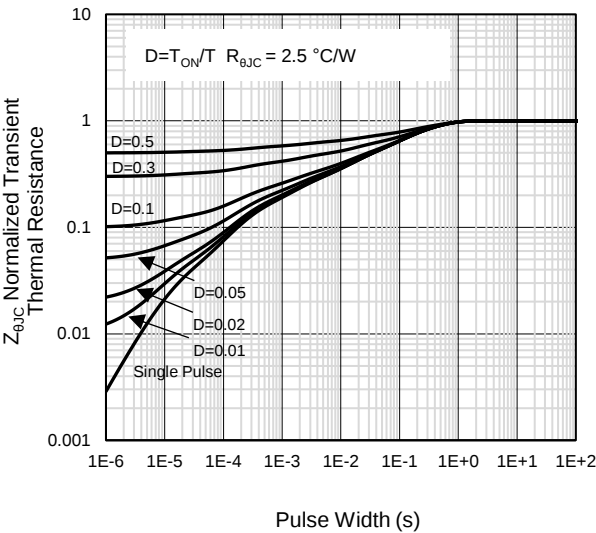


Figure 13: Normalized Maximum Transient Thermal Impedance

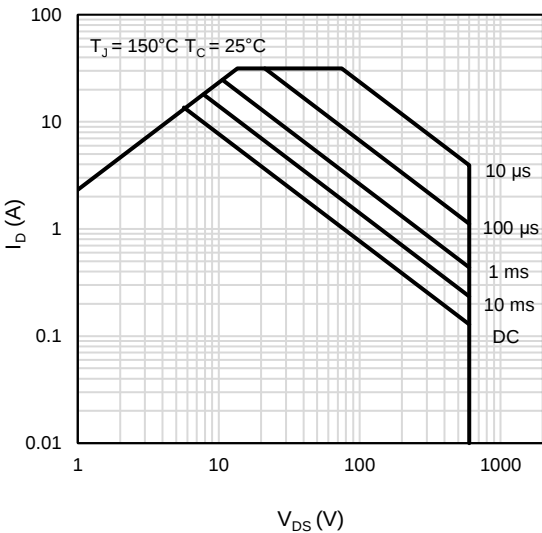
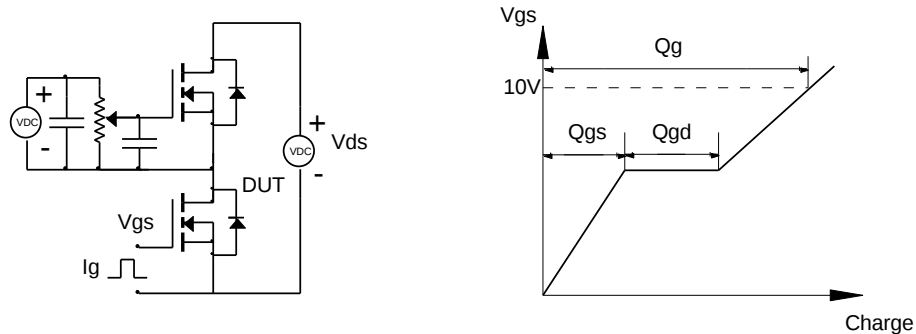


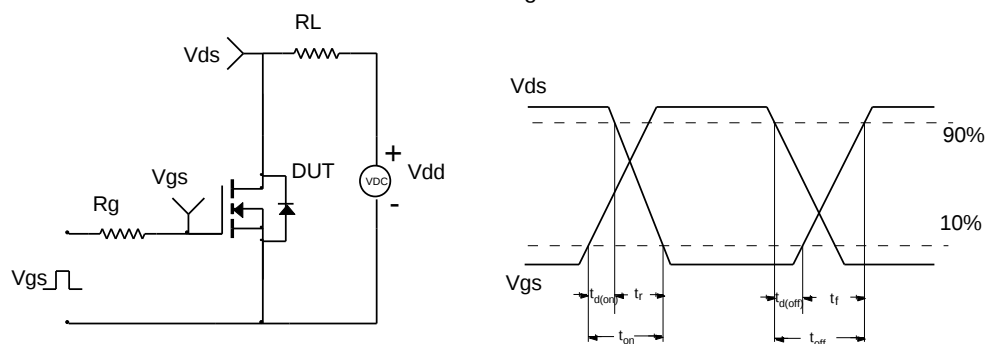
Figure 14: Maximum Forward Biased Safe Operating Area

Test Circuit and Waveform

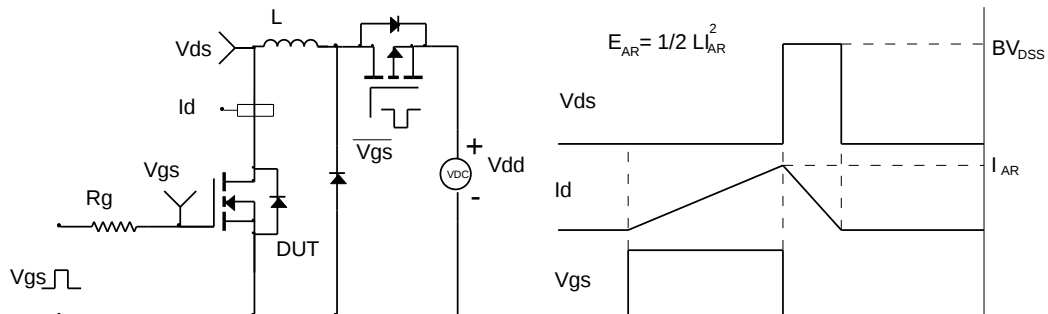
Gate Charge Test Circuit & Waveform



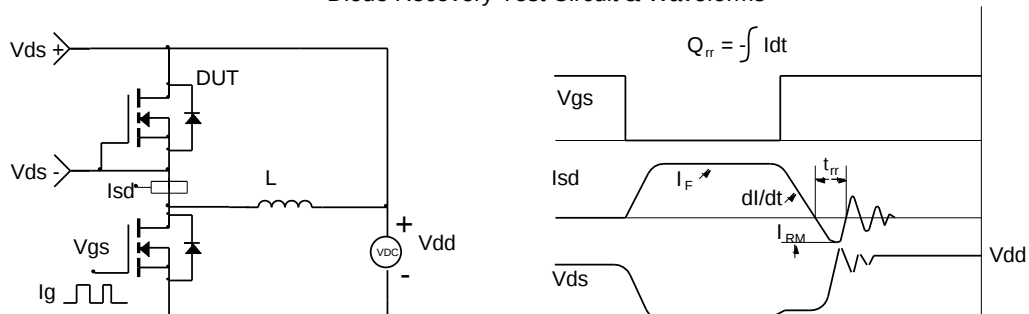
Resistive Switching Test Circuit & Waveforms



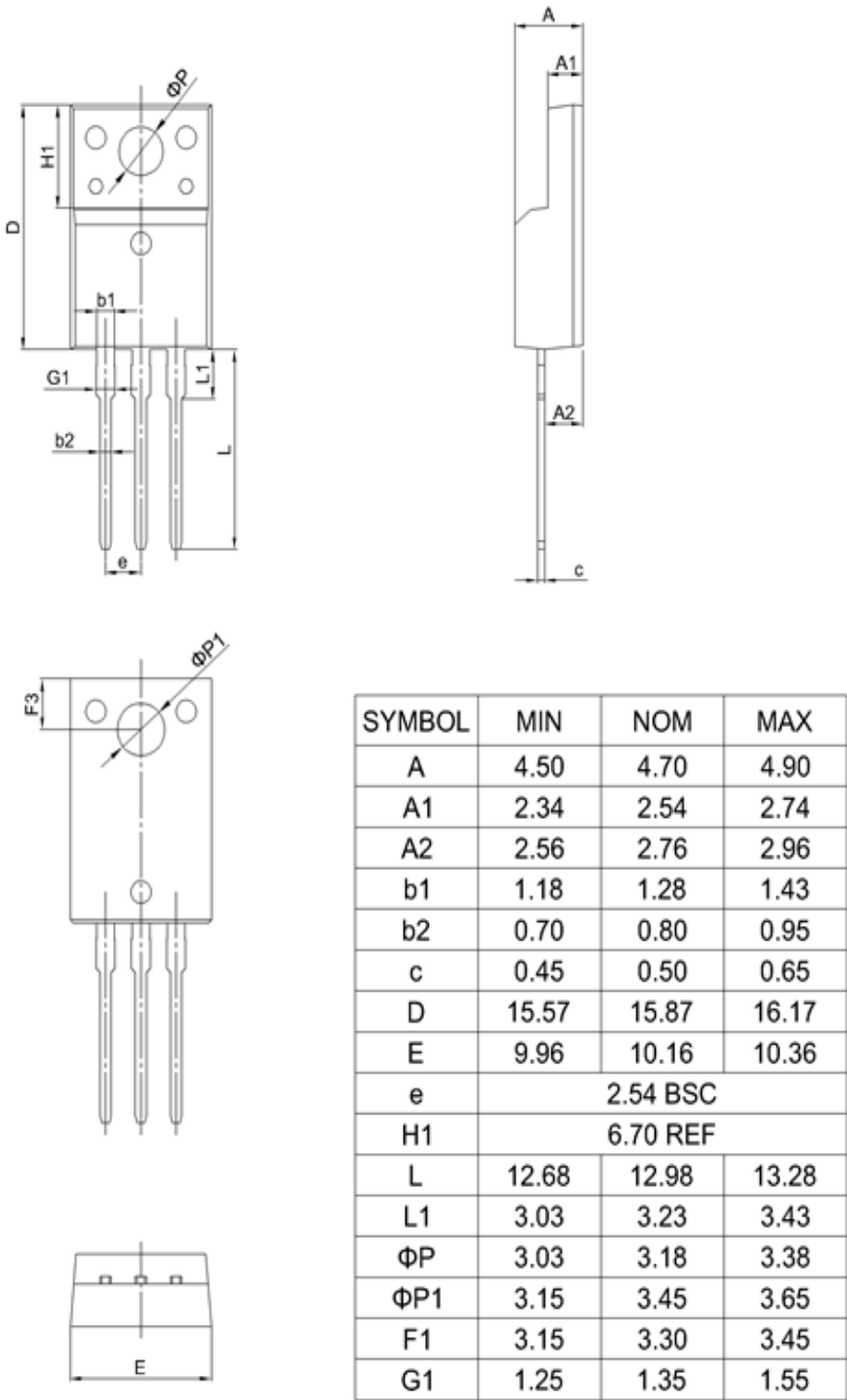
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outlines



Unit in mm

Marking Information



3S60N1K8FMF

XXXXXXX

Note:

3S60N1K8FMF = Product Name Code

XXXXXXX = Date code

Contact ALKAIDSEMI sales for detail information

Revision History

Revision	Released	Remark
Rev.1.0	2024	Initial Release

Disclaimer

The information given in this document describes the independent performance of the product, but similar performance is not guaranteed under other working conditions, and cannot be guaranteed when installed with other products or equipment. To achieve the required performance of the product in actual scenarios, the customer should conduct a complete application test to assess the functionality of the product.

Alkaidsemi assumes no responsibility for equipment failures result from using products at values that exceed the ratings, operating conditions, or other parameters listed in the product specifications.

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